查询CGD1042HI供 CGD1042HI

1 GHz, 22 dB gain GaAs high output power doubler Rev. 2 — 29 September 2010 Produc

Product data sheet

1. **Product profile**

1.1 General description

Hybrid amplifier module in a SOT115J package, operating at a supply voltage of 24 V (DC), employing Hetero junction Field Effect Transistor (HFET) GaAs dies.

1.2 Features and benefits

- Excellent linearity
- Superior levels of ESD protection
- Extremely low noise
- Excellent return loss properties
- Gain compensation over temperature
- Rugged construction
- Unconditionally stable
- Thermally optimized design
- Compliant with Directive 2002/95/EC, regarding Restriction of the use of certain Hazardous Substances (RoHS)
- Integrated ring wave surge protection

1.3 Applications

CATV systems operating in the 40 MHz to 1003 MHz frequency range

1.4 Quick reference data

Table 1. Quick reference data

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 V (DC)$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G _p	power gain	f = 50 MHz	-	21.5	-	dB
		f = 1003 MHz	22	22.7	23.5	dB
СТВ	composite triple beat	V_{o} = 56.4 dBmV at 1003 MHz	<u>[1]</u> -	-75	-65	dBc
CCN	carrier-to-composite noise	V_{o} = 56.4 dBmV at 1003 MHz	<u>[1]</u> 57	63		dBc
I _{tot}	total current		[2] -	440	460	mA

- [1] 79 NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1003 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1003 MHz.
- [2] Direct Current (DC).





1 GHz, 22 dB gain GaAs high output power doubler

2. Pinning information

Table 2.	Pinning	
Pin	Description	Simplified outline Graphic symbol
1	input	
2, 3	common	1 3 5 7 9 5
5	+V _B	
7, 8	common	
9	output	2 3 7 6 sym095

3. Ordering information

Table 3. Ord	ering inf	ormation			
Type number	Packag	age			
	Name	Description	Version		
CGD1042HI	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J		

4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
VB	supply voltage			-	30	V
V _{i(RF)}	RF input voltage	single tone		-	75	dBmV
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E	[1]	-	2000	V
		Biased; According IEC61000-4-2		-	1500	V
T _{stg}	storage temperature			-40	+100	°C
T _{mb}	mounting base temperature			-20	+100	°C

[1] The ESD pulse of 2000 V corresponds to a class 2 sensitivity level.

1 GHz, 22 dB gain GaAs high output power doubler

5. Characteristics

Table 5. Characteristics

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 V (DC)$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 °C$; unless otherwise specified.

	, 2 ,						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
G _p	power gain	f = 50 MHz		-	21.5	-	dB
		f = 1003 MHz		22	22.7	23.5	dB
SL _{sl}	slope straight line	f = 40 MHz to 1003 MHz	[1]	0.5	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 1003 MHz	[2]	-	-	1	dB
RL _{in}	input return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		19	-	-	dB
		f = 640 MHz to 870 MHz		17	-	-	dB
		f = 870 MHz to 1003 MHz		16	-	-	dB
RL _{out}	output return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		19	-	-	dB
		f = 640 MHz to 870 MHz		18	-	-	dB
		f = 870 MHz to 1003 MHz		17	-	-	dB
NF	noise figure	f = 50 MHz		-	4.6	5.6	dB
		f = 1003 MHz		-	5.5	6.5	dB
I _{tot}	total current		[3]	-	440	460	mA
79 NTSC	channels + 75 digital channels						
CTB	composite triple beat	$V_o = 56.4 \text{ dBmV}$ at 1003 MHz	[4]	-	-75	-65	dBc
CSO	composite second-order distortion	$V_o = 56.4 \text{ dBmV}$ at 1003 MHz	[4]	-	-77	-65	dBc
Xmod	cross modulation	$V_o = 56.4 \text{ dBmV}$ at 1003 MHz	[4]	-	-68	-	dB
CCN	carrier-to-composite noise	$V_o = 56.4 \text{ dBmV}$ at 1003 MHz	[4]	57	63	-	dBc
79 NTSC channels							
СТВ	composite triple beat	$V_o = 58.4 \text{ dBmV}$ at 1003 MHz	[5]	-	-70	-	dBc
CSO	composite second-order distortion	$V_o = 58.4 \text{ dBmV}$ at 1003 MHz	[5]	-	-75	-	dBc
Xmod	cross modulation	$V_o = 58.4 \text{ dBmV}$ at 1003 MHz	[5]	-	-65	-	dB

[1] G_p at 1003 MHz minus G_p at 40 MHz.

[2] Flatness is defined as peak deviation to straight line.

[3] Direct Current (DC).

[4] 79 NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1003 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1003 MHz.

[5] 79 NTSC channels [f = 54 MHz to 550 MHz]; tilt extrapolated to 13.5 dB at 1003 MHz.

NAPUSERNICOARDUCTORS

CGD1042HI

1 GHz, 22 dB gain GaAs high output power doubler

6. Package outline

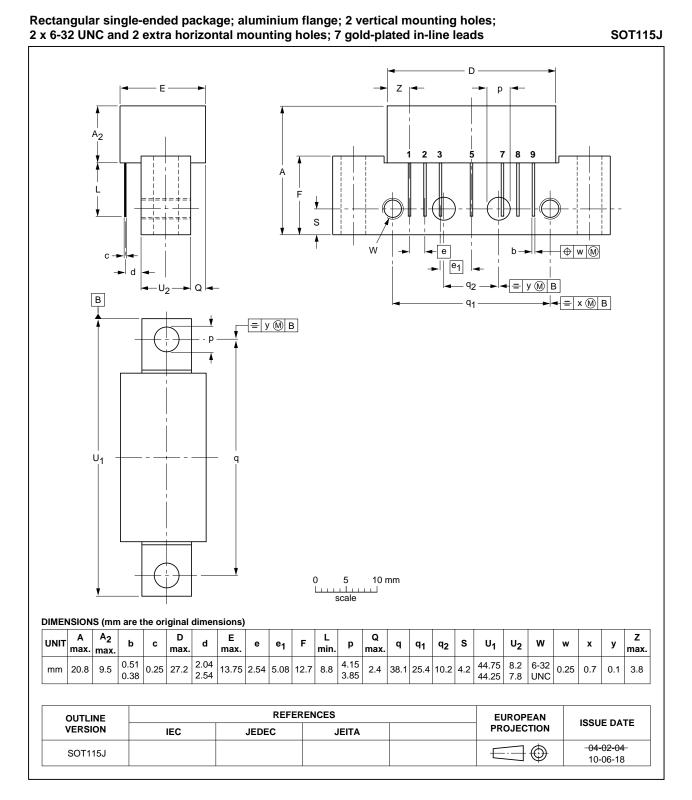


Fig 1. Package outline SOT115J

All information provided in this document is subject to legal disclaimers.

CGD1042HI

1 GHz, 22 dB gain GaAs high output power doubler

7. Abbreviations

Table 6.	Abbreviations		
Acronym	Description		
CATV	Community Antenna TeleVision		
DC	Direct Current		
ESD	ElectroStatic Discharge		
GaAs	Gallium-Arsenide		
NTSC	National Television Standard Committee		
RF	Radio Frequency		
UNC	UNified Coarse		

8. Revision history

Table 7. Revisi	on history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
CGD1042HI v.2	20100929	Product data sheet	-	CGD1042HI v.1
Modifications:	•	line drawings have been update ave been updated.	ed to the latest version.	
CGD1042HI v.1	20090921	Product data sheet	-	-

1 GHz, 22 dB gain GaAs high output power doubler

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

9.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

9.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

1 GHz, 22 dB gain GaAs high output power doubler

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Non-automotive qualified products — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the

10. Contact information

product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

9.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

1 GHz, 22 dB gain GaAs high output power doubler

11. Contents

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Limiting values 2
5	Characteristics 3
6	Package outline 4
7	Abbreviations 5
8	Revision history 5
9	Legal information 6
9.1	Data sheet status 6
9.2	Definitions6
9.3	Disclaimers 6
9.4	Trademarks 7
10	Contact information 7
11	Contents 8

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2010.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 29 September 2010 Document identifier: CGD1042HI